

47. (Amended) A method according to claim 45, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between a solid state and a liquid state.

48. (Amended) A method according to claim 45, wherein said gate oxide film is continuously formed without exposing the air after forming said semiconductor film.

49. (Amended) A method for manufacturing a semiconductor device comprising steps of:

C1
Cmcd
contacting a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;
subjecting said semiconductor film to plasma comprising oxygen and helium; and
irradiating said semiconductor film with an infrared ray or a laser light.

50. (Amended) A method according to claim 49, wherein said semiconductor film is crystallized through a solid state or intermediate state between a solid state and a liquid state.

Sub
P2
C2
52. (Twice Amended) A method for manufacturing a semiconductor device comprising steps of:

contacting a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;
subjecting said semiconductor film to oxygen plasma; and
crystallizing said semiconductor film using said material, to obtain a crystalline semiconductor film.

C3
53. (Amended) A method according to claim 52, wherein said crystallizing is performed by crystallizing said semiconductor film by irradiating with an infrared ray or a laser light.

54. (Amended) A method according to claim 52, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between a solid state and a liquid state.

Sub
P3

56. (Amended) A method for manufacturing a semiconductor device comprising steps of:

contacting a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;

subjecting said semiconductor film to oxygen plasma;

irradiating said semiconductor film with an infrared ray or a laser light; and

patterning said crystalline semiconductor film.

57. (Amended) A method according to claim 56, further comprising a step of forming a second gate insulating film on the patterned semiconductor film.

C4
Sub
P4

58. (Amended) A method according to claim 56, wherein said semiconductor film is crystallized through a solid state or intermediate state between a solid state and a liquid state.

59. (Amended) A method according to claim 56, wherein an oxide film of said semiconductor film is formed thereon by said oxygen plasma.

Sub
P5

60. (Amended) A method for manufacturing a semiconductor device comprising steps of:

C5
Cmt

contacting at least one metal element to at least a part of a semiconductor film formed over a substrate;

subjecting said semiconductor film to plasma;

crystallizing said semiconductor film to obtain a crystalline semiconductor film; and

patterning said crystalline semiconductor film.

61. (Amended) A method according to claim 60, wherein said crystallizing is performed by crystallizing said semiconductor film by irradiating with an infrared ray or a laser light.

62. (Amended) A method according to claim 60, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between a solid state and a liquid state.

63. (Amended) A method according to claim 60, wherein a gate insulating film of said semiconductor film is formed thereon by said plasma.

Sub
Du
CS
Cmid
64. (Amended) A method for manufacturing a semiconductor device comprising steps of:

contacting at least one metal element to at least a part of a semiconductor film formed over a substrate;

subjecting said semiconductor film to plasma; and

irradiating said semiconductor film with an infrared ray or a laser light.

65. (Amended) A method according to claim 64, wherein said semiconductor film is crystallized through a solid state or intermediate state between a solid state and a liquid state.

66. (Amended) A method according to claim 64, wherein a first gate insulating film of said semiconductor film is formed thereon by said plasma.

Please add new claims 67-72 as follows:

67. A method according to claim 45, wherein said material for promoting crystallization is selected from the group consisting of Ni, Fe, Co, Pt, Cu, Au, Ge, Ru, Rh, Pd, Os, Ir, and Pb.

Cl
Cmt
68. A method according to claim 49, wherein said material for promoting crystallization is selected from the group consisting of Ni, Fe, Co, Pt, Cu, Au, Ge, Ru, Rh, Pd, Os, Ir, and Pb.

69. A method according to claim 52, wherein said material for promoting crystallization is selected from the group consisting of Ni, Fe, Co, Pt, Cu, Au, Ge, Ru, Rh, Pd, Os, Ir, and Pb.

70. A method according to claim 56, wherein said material for promoting crystallization is selected from the group consisting of Ni, Fe, Co, Pt, Cu, Au, Ge, Ru, Rh, Pd, Os, Ir, and Pb.

71. A method according to claim 60, wherein said metal element for promoting crystallization is selected from the group consisting of Ni, Fe, Co, Pt, Cu, Au, Ge, Ru, Rh, Pd, Os, and Ir.

Chcid
72. A method according to claim 64, wherein said metal element for promoting crystallization is selected from the group consisting of Ni, Fe, Co, Pt, Cu, Au, Ge, Ru, Rh, Pd, Os, and Ir.
